

# MegaMOS™ FET

IXTH / IXTM 67N10  
IXTH / IXTM 75N10

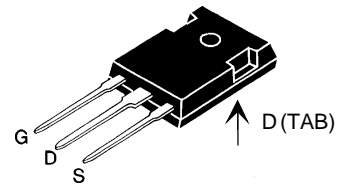
$V_{DSS}$	$I_{D25}$	$R_{DS(on)}$
100 V	67 A	25 mΩ
100 V	75 A	20 mΩ

## N-Channel Enhancement Mode

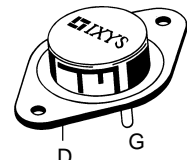


Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	100	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1\text{ M}\Omega$	100	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	67N10	67 A
		75N10	75 A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	67N10	268 A
		75N10	300 A
$P_D$	$T_C = 25^\circ\text{C}$	300	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$M_d$	Mounting torque	1.13/10	Nm/lb.in.
<b>Weight</b>		TO-204 = 18 g, TO-247 = 6 g	
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-247 AD (IXTH)



TO-204 AE (IXTM)



G = Gate, D = Drain,  
S = Source, TAB = Drain

### Features

- International standard packages
- Low  $R_{DS(on)}$  HDMOS™ process
- Rugged polysilicon gate cell structure
- Low package inductance (< 5 nH)
  - easy to drive and to protect
- Fast switching times

### Applications

- Switch-mode and resonant-mode power supplies
- Motor controls
- Uninterruptible Power Supplies (UPS)
- DC choppers

### Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

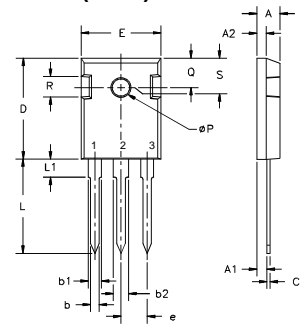
Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\ \mu\text{A}$	100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$	2		V
$I_{GSS}$	$V_{GS} = \pm 20\text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 100\text{ nA}$
$I_{DSS}$	$V_{DS} = 0.8 \cdot V_{DSS}$ $V_{GS} = 0\text{ V}$	$T_J = 25^\circ\text{C}$		200 $\mu\text{A}$
		$T_J = 125^\circ\text{C}$		1 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 0.5\ I_{D25}$ Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$	67N10		0.025 $\Omega$
		75N10		0.020 $\Omega$

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)			
		min.	typ.	max.	
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = 0.5 I_{D25}$ , pulse test	25	30	S	
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4500	pF	
$C_{oss}$			1300	pF	
$C_{rss}$			550	pF	
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 2\ \Omega$ , (External)		40	60	ns
$t_r$			60	110	ns
$t_{d(off)}$			100	140	ns
$t_f$			30	60	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$		180	260	nC
$Q_{gs}$			30	70	nC
$Q_{gd}$			90	160	nC
$R_{thJC}$			0.42	K/W	
$R_{thCK}$			0.25	K/W	

### Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)			
		min.	typ.	max.	
$I_S$	$V_{GS} = 0\text{ V}$	67N10 75N10		67 75	A A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$	67N10 75N10		268 300	A A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.75	V
$t_{rr}$	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		300		ns

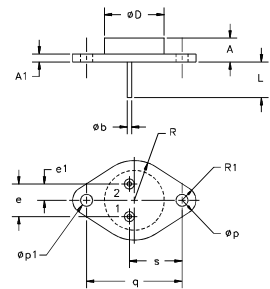
### TO-247 AD (IXTH) Outline



Terminals: 1 - Gate 2 - Drain  
3 - Source Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

### TO-204AE (IXTM) Outline



Pins 1 - Gate 2 - Source  
Case - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	6.4	11.4	.250	.450
A <sub>1</sub>	1.53	3.42	.060	.135
Øb	1.45	1.60	.057	.063
ØD		22.22		.875
e	10.67	11.17	.420	.440
e <sub>1</sub>	5.21	5.71	.205	.225
L	11.18	12.19	.440	.480
Øp	3.84	4.19	.151	.165
Øp <sub>1</sub>	3.84	4.19	.151	.165
q	30.15	BSC	1.187	BSC
R	12.58	13.33	.495	.525
R <sub>1</sub>	3.33	4.77	.131	.188
s	16.64	17.14	.655	.675

Fig. 1 Output Characteristics

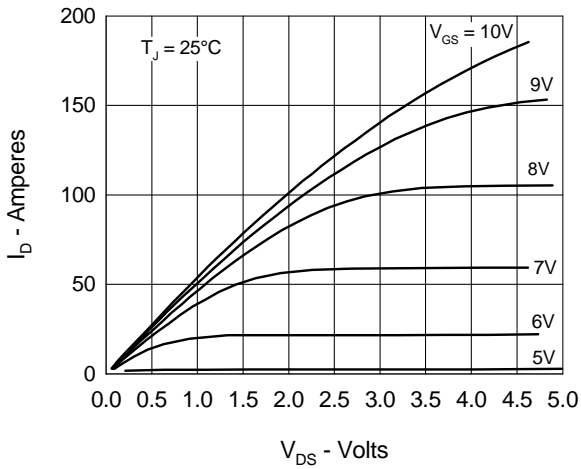


Fig. 2 Input Admittance

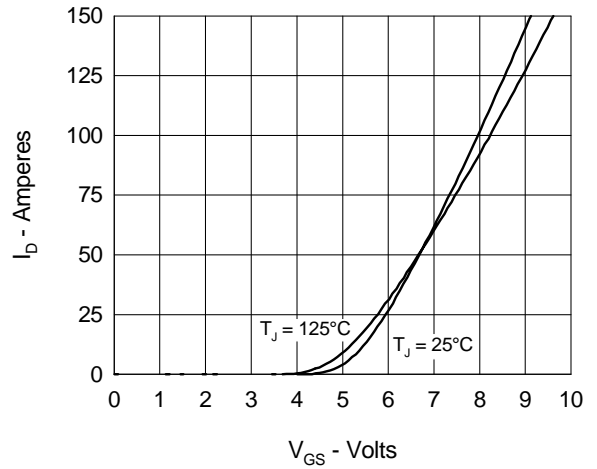


Fig. 3  $R_{DS(on)}$  vs. Drain Current

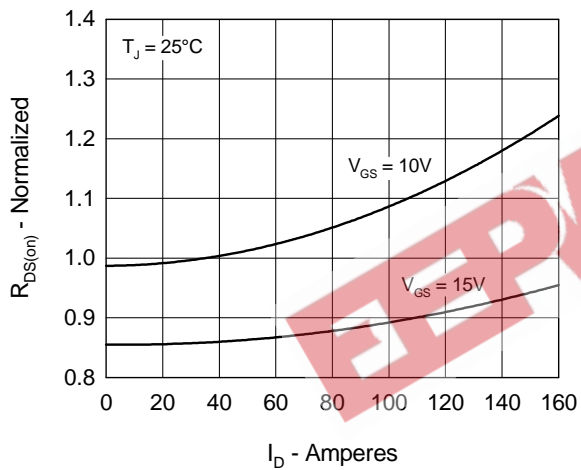


Fig. 4 Temperature Dependence of Drain to Source Resistance

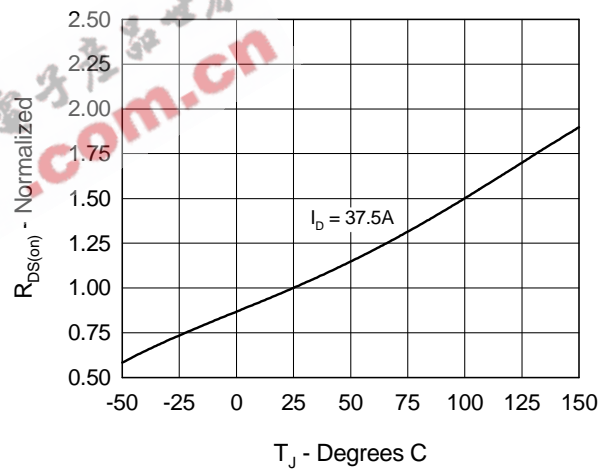


Fig. 5 Drain Current vs. Case Temperature

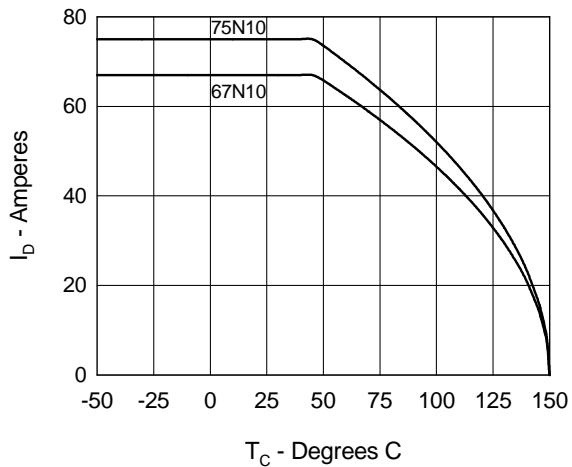


Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage

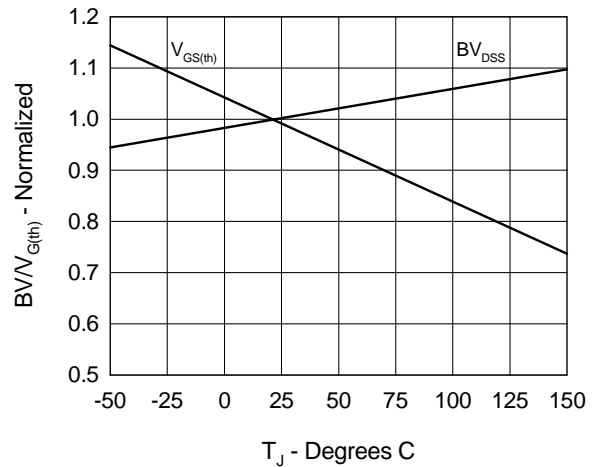


Fig.7 Gate Charge Characteristic Curve

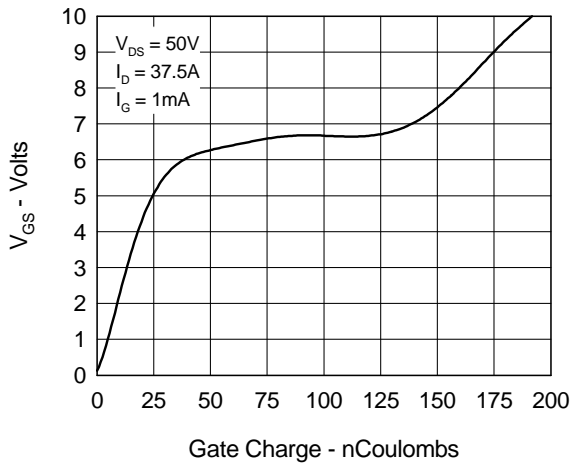


Fig.8 Forward Bias Safe Operating Area

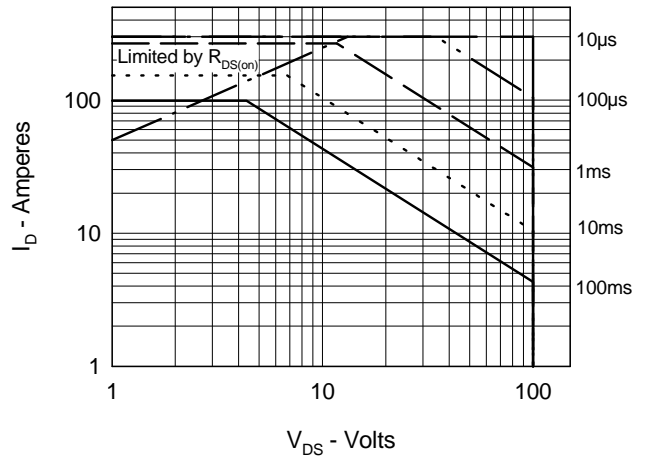


Fig.9 Capacitance Curves

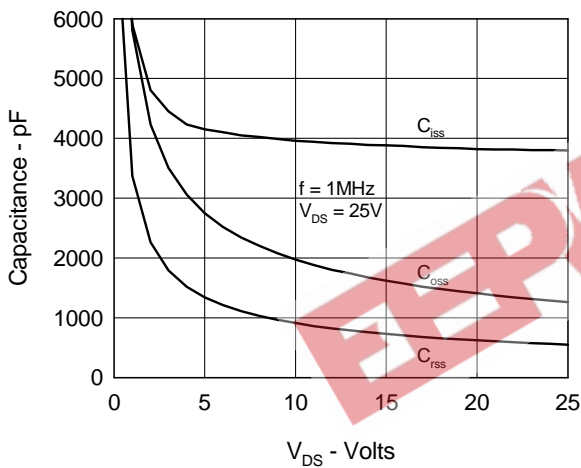


Fig.10 Source Current vs. Source to Drain Voltage

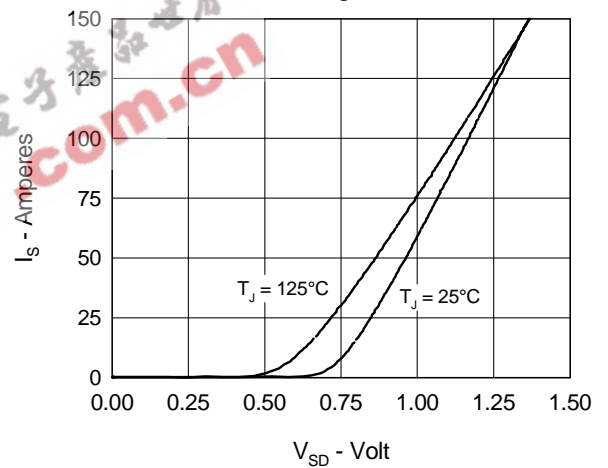


Fig.11 Transient Thermal Impedance

